

## FEATURES

- ◆ Ultra Broad Bandwidth: 50 MHz to 50 GHz
- ◆ Functional Bandwidth : 50 MHz to 70 GHz
- ◆ 0.7 dB Insertion Loss,
- ◆ 33 dB Isolation at 50 GHz
- ◆ Low Current consumption.
  - -10mA for low loss state
  - +10mA for Isolation state
- ◆ M/A-COM's unique AlGaAs hetero-junction anode technology.
- ◆ Silicon Nitride Passivation
- ◆ Polyimide Scratch protection

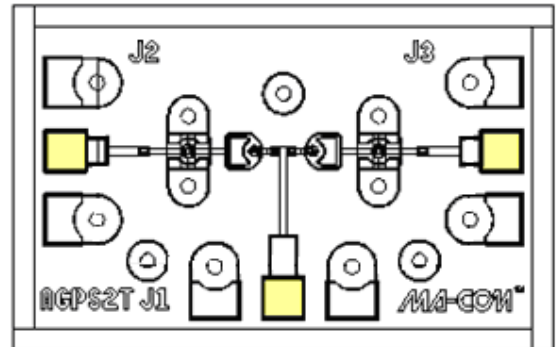
## DESCRIPTION

M/A-COM's MA4AGSW2 is an Aluminum-Gallium-Arsenide anode enhanced, SP2T PIN diode switch. AlGaAs anodes, which utilize M/A-COM's patented hetero-junction technology, which produces less loss than conventional GaAs processes, as much as 0.3 dB reduction in insertion loss at 50 GHz.. These devices are fabricated on an OMCVD epitaxial wafer using a process designed for high device uniformity and extremely low parasitics. The diodes themselves exhibit low series resistance, low capacitance, and fast switching speed. They are fully passivated with silicon nitride and have an additional layer of a polymer for scratch protection. The protective coating prevents damage to the junction and the anode air-bridges during handling. Off-chip bias circuitry is required and allows maximum design flexibility.

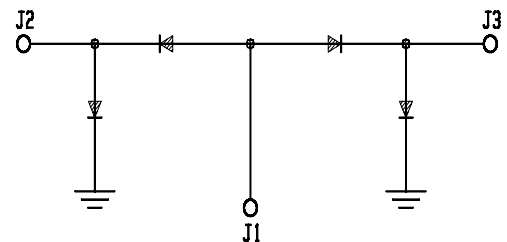
## APPLICATIONS

The low capacitance of the PIN diodes used makes it ideal for use in microwave multi-throw switch designs, where the series capacitance in each off-arm will load the input. Also, the low series resistance of the diodes helps the total insertion loss of the devices at microwave frequencies. These AlGaAs PIN switches are used as the switching arrays for radar systems, radiometers, and other multi-assembly components.

## CHIP LAYOUT



Yellow areas indicate bond pads



## ABSOLUTE MAXIMUM RATINGS<sup>1</sup>

@ T<sub>A</sub> = +25°C ( Unless otherwise specified )

PARAMETER	MAXIMUM RATING
OPERATING TEMPERATURE	-55° TO +125°c
STORAGE TEMPERATURE	-65°C TO +150°C
INCIDENT C.W. RF POWER	+23 dBm C.W.
BREAKDOWN VOLTAGE	25 V
BIAS CURRENT	+/-30 mA

### Note:

Exceeding any of these values may result in permanent damage to chip.

## TYPICAL DRIVER CONNECTIONS

CONTROL LEVEL (DC CURRENT)		RF OUTPUT STATE	
J2	J3	J2-J1	J3-J1
-10mA	+10mA	Low Loss	Isolation
+10mA	-10mA	Isolation	Low Loss

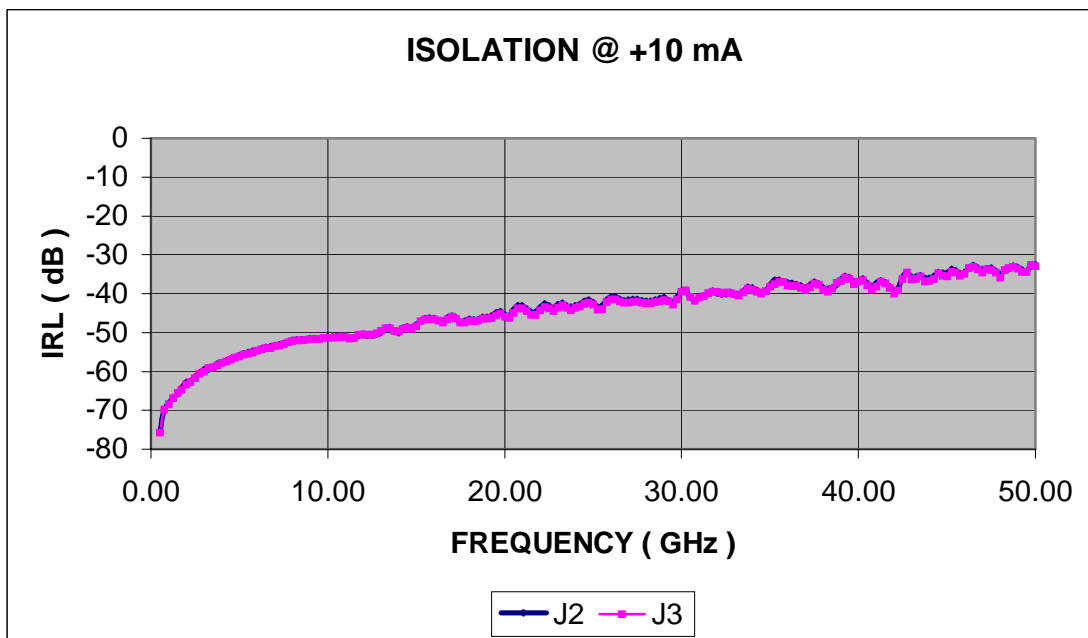
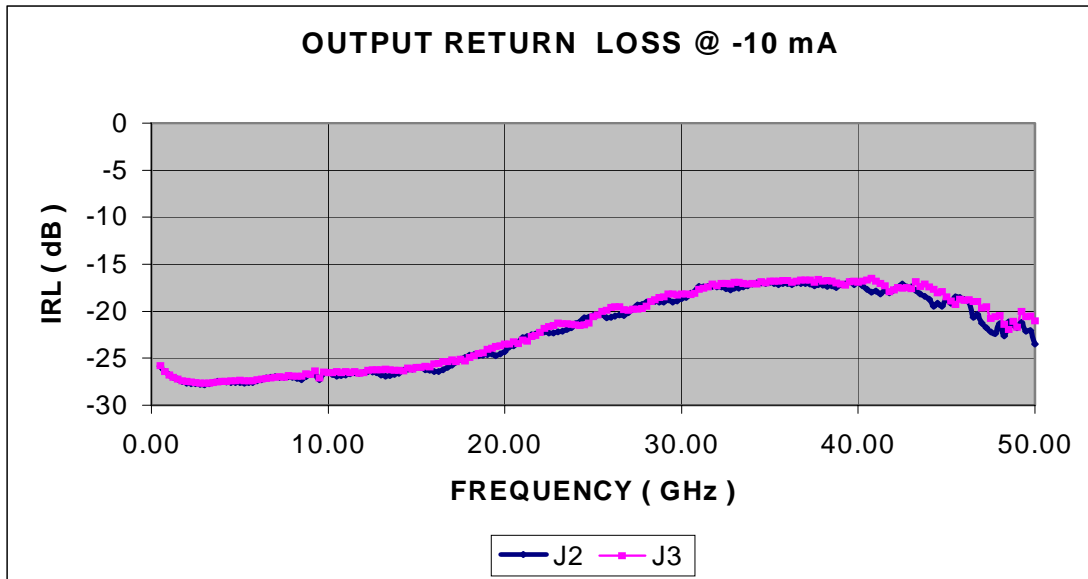
### Electrical Specifications @ $T_A = 25^\circ\text{C}$ , +/-10mA bias current (On-wafer measurements)

RF SPECIFICATIONS					
PARAMETER	FREQUENCY BAND	MIN	TYP	MAX	UNITS
INSERTION LOSS	0.05 - 18GHz	---	0.5	0.6	dB
	18 - 50GHz	---	0.7	0.9	dB
ISOLATION	0.05 - 18GHz	45	47	---	dB
	18 - 50GHz	28	33	---	dB
INPUT RETURN LOSS	0.05 - 18GHz	---	22	---	dB
	18 - 50GHz	---	21	---	dB
OUTPUT RETURN LOSS	0.05 - 18GHz	---	25	---	dB
	18 - 50GHz	---	22	---	dB
SWITCHING SPEED * ( 10 % - 90 % RF VOLTAGE )	10GHz	---	20	---	nS

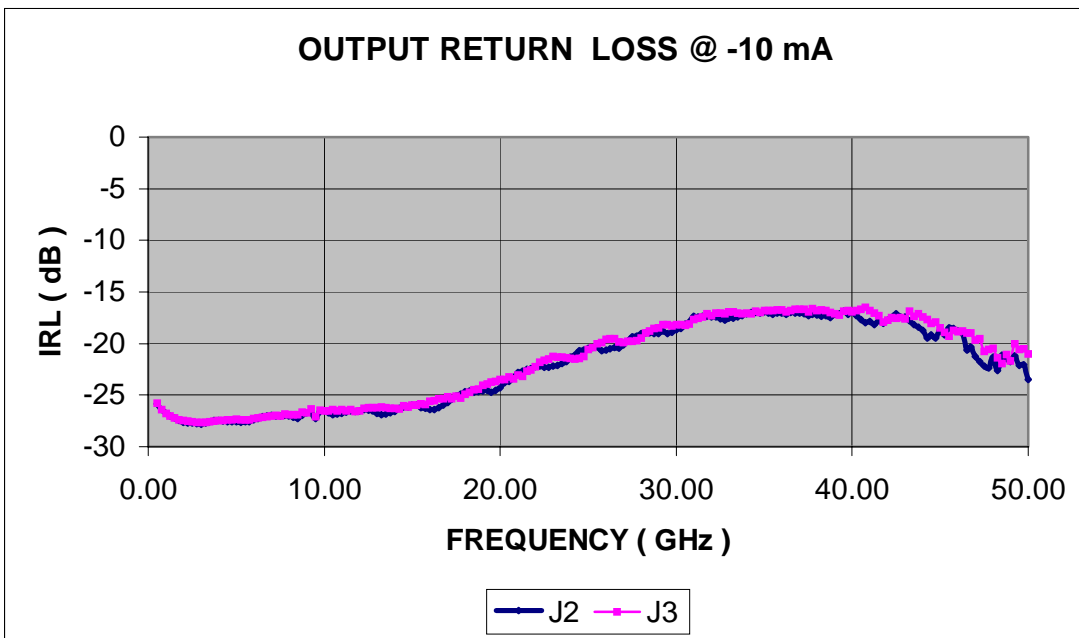
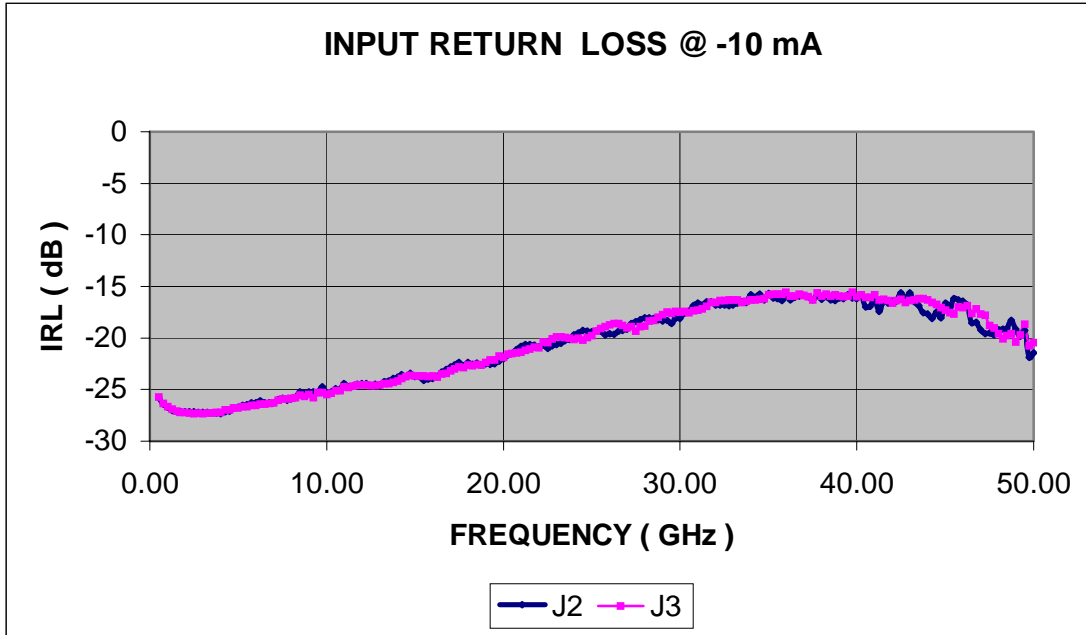
**\*Note:**

Typical switching speed is measured from 10% to 90% of the detected RF voltage driven by a TTL compatible driver. Driver output parallel RC network uses a capacitor between 390 pF - 560 pF and a resistor between 150 - 220 Ohms to achieve 20 ns rise and fall times.

### Typical RF Performance (Probed on Wafer)



### Typical RF Performance (Probed on wafer)

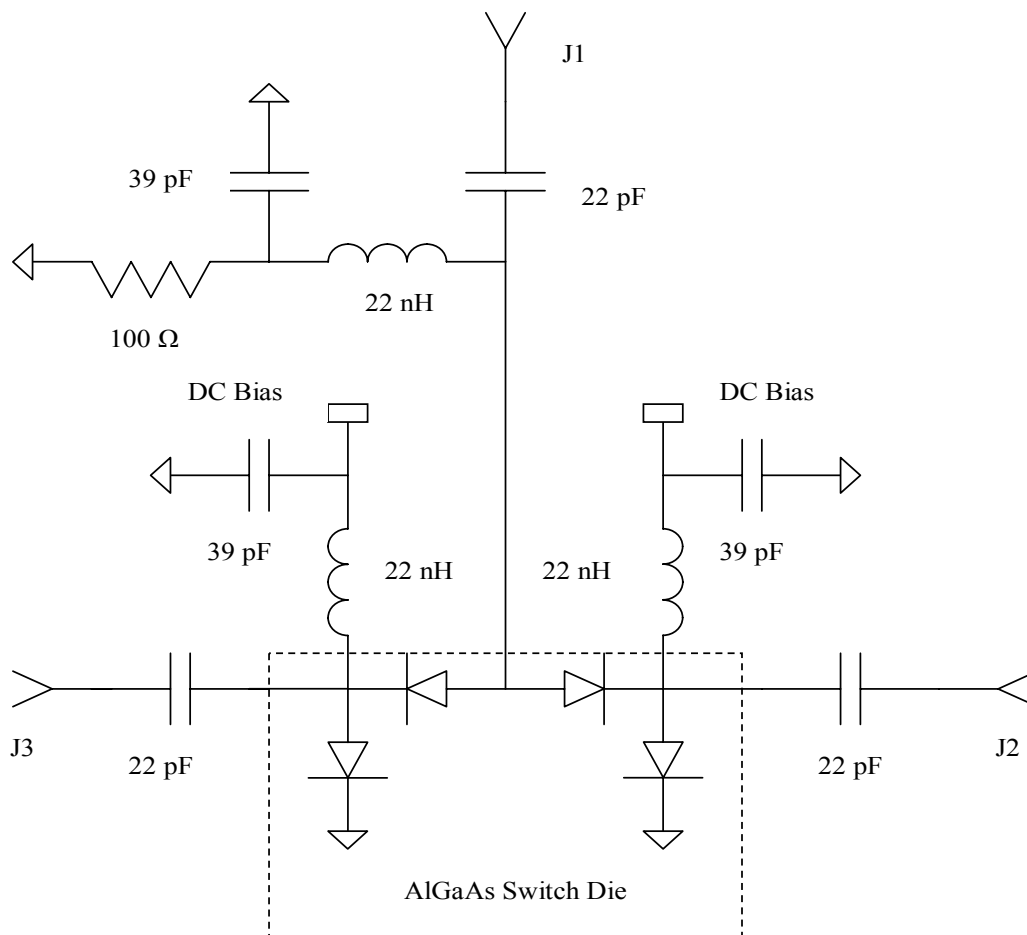


## Operation of the MA4AGSW2 Switch

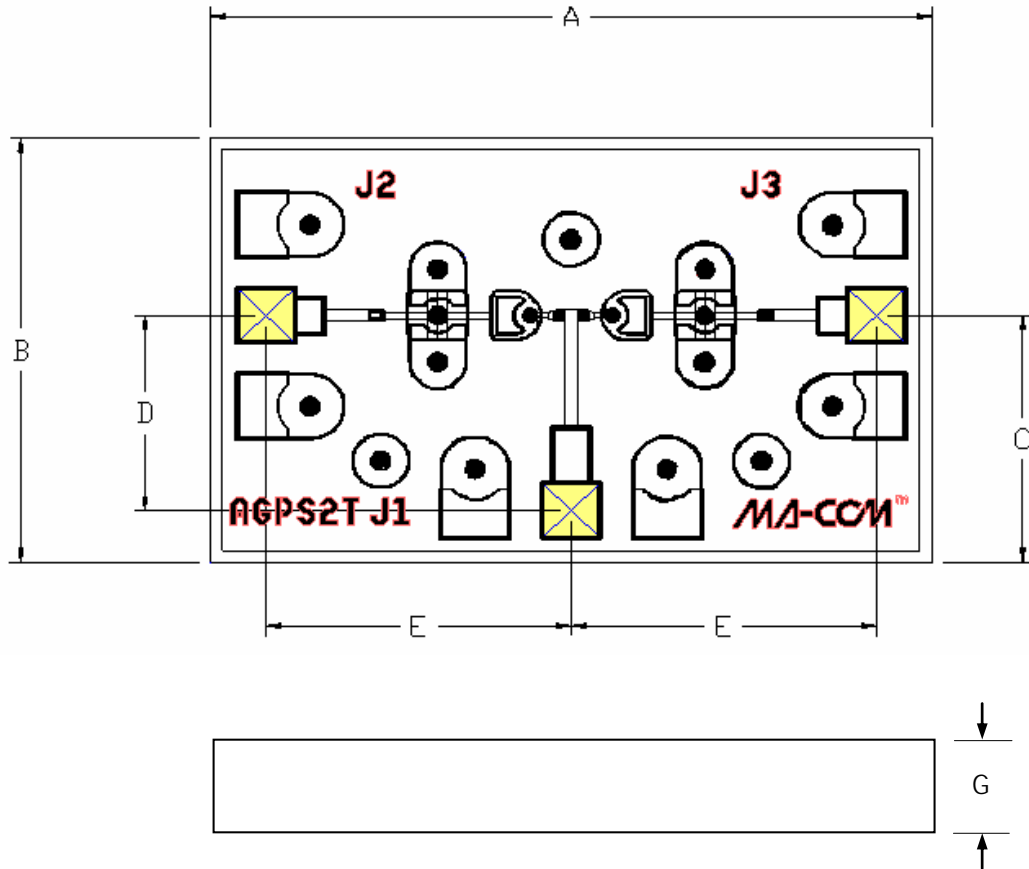
The simultaneous application of negative DC current to the Low Loss Port and positive DC current to the remaining Isolated Switching Ports achieves operation of the MA4AGSW Series of AlGaAs PIN Switches. The backside area of the die is the RF and DC return ground plane. The DC return is achieved on common port J1. constant current sources should supply the DC control currents. The diode voltages at these bias nodes will not exceed  $\pm 1.6$  volts (+ 1.4 volts typical for Supply Currents up to  $\pm 30$ mA). In the Low Loss State, the series diode must be forward biased and the shunt diode reverse biased. For all the Isolated Ports, the shunt diode is forward biased and the Series Diode is reverse biased. The bias network design should yield > 30 dB RF to DC Isolation.

Best Insertion Loss, P1dB, IP3, and Switching Speed is achieved by using a Voltage Pull-up Resistor in the DC Return Path, (J1). A minimum value of | -2V | is recommended at this return node, which is achievable with a standard, +/-5V TTL Controlled PIN Diode Driver.

**MA4AGSW2 Schematic with 2-18 GHz Bias Network**



## Chip Dimensions and Pad Locations (In Yellow)



DIM	mils			mm		
	Min.	Typical	Max.	Min.	Typical	Max.
A	48	49	50	1.22	1.24	1.27
B	29.7	30.7	31.7	0.75	0.78	0.8
C	17.3	17.8	18.3	0.44	0.45	0.46
D	13.7	13.9	14.1	0.35	0.35	0.36
E	20.3	20.5	20.7	0.52	0.52	0.53
F	3.7	4	4.3	0.09	0.1	0.11
G	3.7	3.9	4.3	0.09	0.1	0.11
Thickness	.009	.010	.011	.00023	.00025	.00028
Pads X-Y	.0035	.0040	.0045	.0889	.1016	.1143

## **ASSEMBLY INSTRUCTIONS**

The following precautions should be observed to avoid damaging these chips.

### **CLEANLINESS**

These chips should be handled in a clean environment.

### **STATIC SENSITIVITY**

These Devices are considered ESD Class1. Proper ESD techniques should be used when handling these devices.

### **GENERAL HANDLING**

The protective polymer coating on the active areas of these die provides scratch and impact protection, particularly for the metal air bridge, which contacts the diode's anode. Die should primarily be handled with vacuum pickups, or alternatively with plastic tweezers.

## **ASSEMBLY TECHNIQUES**

These AlGaAs devices are designed to be mounted with electrically conductive silver epoxy or with a lower temperature solder perform, which is not rich in Sn content.

### **SOLDER DIE ATTACH**

All die attach and bonding methods should be compatible with gold metal. Solder which does not scavenge gold, such as 80/20, Au/Sn or Indalloy #2 is recommended. Do not expose die to a temperature greater than 300°C for more than 10 seconds.

### **ELECTRICAL CONDUCTIVE EPOXY DIE ATTACH**

Assembly can be preheated to approximately 125°C. Use a controlled thickness of approximately 2 mils for best electrical conductivity and lower thermal resistance. Cure epoxy as per manufacturer's schedule. For extended cure times, temperatures should be kept below 150°C.

### **RIBBON/WIRE BONDING**

Wedge thermo compression bonding or ball bonding may be used to attach ribbons to the bonding pads. Gold ribbons should be 1/4 x 3 mil sq. for all RF ports for lowest inductance and best microwave performance.

## **Ordering Information**

Part Number	Package
MA4AGSW2	Waffle Pack
MASW-000552-13210G	Gel Pack